

V_{DSS}	-12V
$R_{DS(on)}(Max.)$	26mΩ
I_D	±5A
P_D	1.25W

●Features

- 1) Low on - resistance.
- 2) High power package
- 3) Low voltage drive(1.5V)

●Application

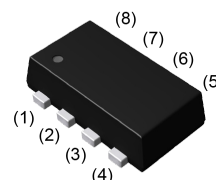
Switching

●Absolute maximum ratings ($T_a = 25^{\circ}C$)

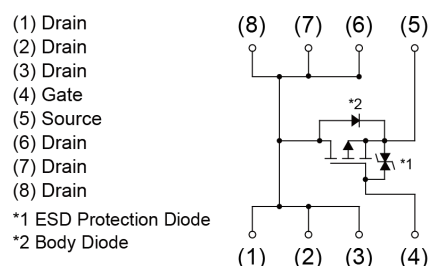
Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	-12	V
Continuous drain current	I_D	±5	A
Pulsed drain current	$I_{D,pulse}^{*1}$	±20	A
Gate - Source voltage	V_{GSS}	±10	V
Power dissipation	P_D^{*2}	1.25	W
	P_D^{*3}	0.6	W
Junction temperature	T_j	150	°C
Range of storage temperature	T_{stg}	-55 to +150	°C

●Outline

TSST8



●Inner circuit



●Packaging specifications

Type	Packing	Embossed Tape
	Reel size (mm)	180
	Tape width (mm)	8
	Basic ordering unit (pcs)	3000
	Taping code	TR
	Marking	YH

● Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - ambient	R_{thJA}^{*2}	-	-	100	°C/W
	R_{thJA}^{*3}	-	-	208	°C/W

● Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -1mA$	-12	-	-	V
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_j}$	$I_D = -1mA$ referenced to 25°C	-	-21.9	-	mV/°C
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -12V, V_{GS} = 0V$	-	-	-1	μA
Gate - Source leakage current	I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0V$	-	-	±10	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = -6V, I_D = -1mA$	-0.3	-	-1.0	V
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{GS(th)}}{\Delta T_j}$	$I_D = -1mA$ referenced to 25°C	-	2.4	-	mV/°C
Static drain - source on - state resistance	$R_{DS(on)}^{*4}$	$V_{GS} = -4.5V, I_D = -5A$	-	19	26	mΩ
		$V_{GS} = -2.5V, I_D = -2.5A$	-	26	36	
		$V_{GS} = -1.8V, I_D = -2.5A$	-	34	50	
		$V_{GS} = -1.5V, I_D = -1A$	-	48	96	
Forward Transfer Admittance	$ Y_{fs} ^{*4}$	$V_{DS} = -6V, I_D = -5A$	7	-	-	S

*1 $P_w \leq 10\mu\text{s}$, Duty cycle $\leq 1\%$

*2 Mounted on a ceramic board (30x30x0.8mm)

*3 Mounted on a FR4 (20x20x0.8mm)

*4 Pulsed

●Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	C_{iss}	$V_{GS} = 0V$	-	2800	-	pF
Output capacitance	C_{oss}	$V_{DS} = -6V$	-	340	-	
Reverse transfer capacitance	C_{rss}	$f = 1\text{MHz}$	-	310	-	
Turn - on delay time	$t_{d(on)}^{*4}$	$V_{DD} \approx -6V, V_{GS} = -4.5V$	-	12	-	ns
Rise time	t_r^{*4}	$I_D = -2.5A$	-	95	-	
Turn - off delay time	$t_{d(off)}^{*4}$	$R_L \approx 2.4\Omega$	-	410	-	
Fall time	t_f^{*4}	$R_G = 10\Omega$	-	220	-	

●Gate charge characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q_g^{*4}	$V_{DD} \approx -6V,$	-	34	-	nC
Gate - Source charge	Q_{gs}^{*4}	$I_D = -5A,$	-	6.0	-	
Gate - Drain charge	Q_{gd}^{*4}	$V_{GS} = -4.5V$	-	5.0	-	

●Body diode electrical characteristics (Source-Drain) ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Body diode continuous forward current	I_S	$T_a = 25^\circ\text{C}$	-	-	-1	A
Body diode pulse current	I_{SP}^{*1}		-	-	-20	A
Forward voltage	V_{SD}^{*4}	$V_{GS} = 0V, I_S = -5A$	-	-	-1.2	V

●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

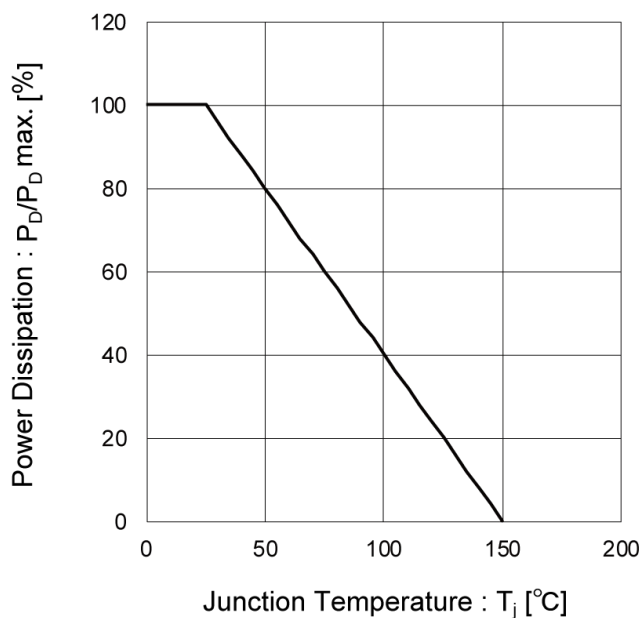


Fig.2 Maximum Safe Operating Area

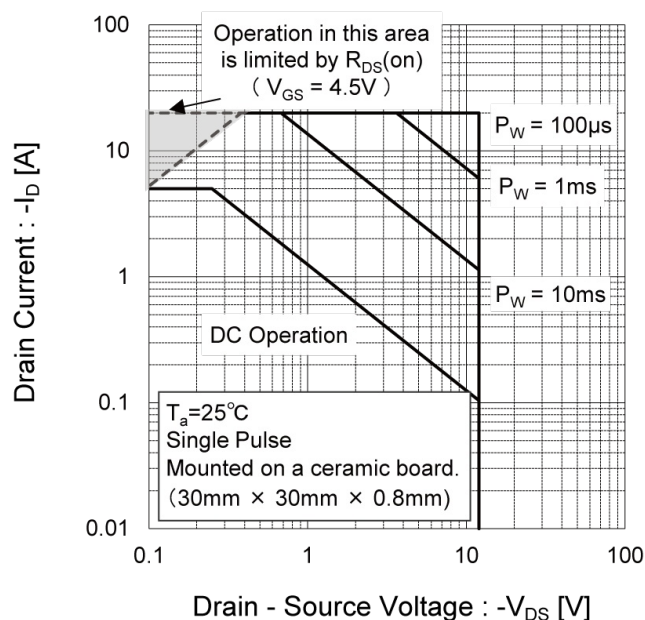


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

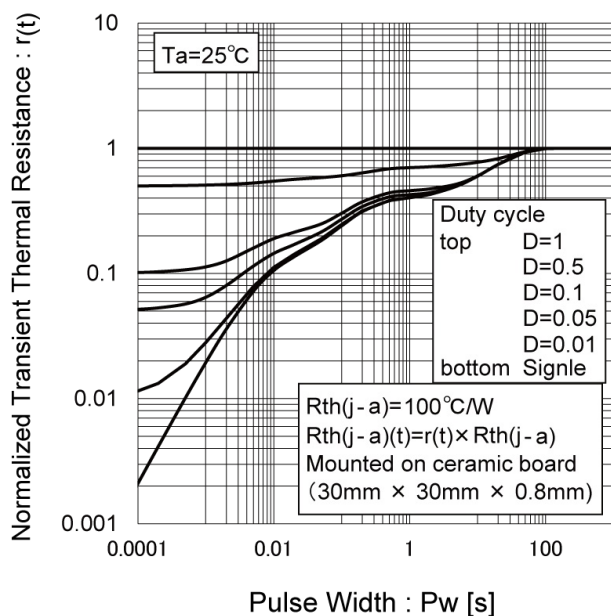
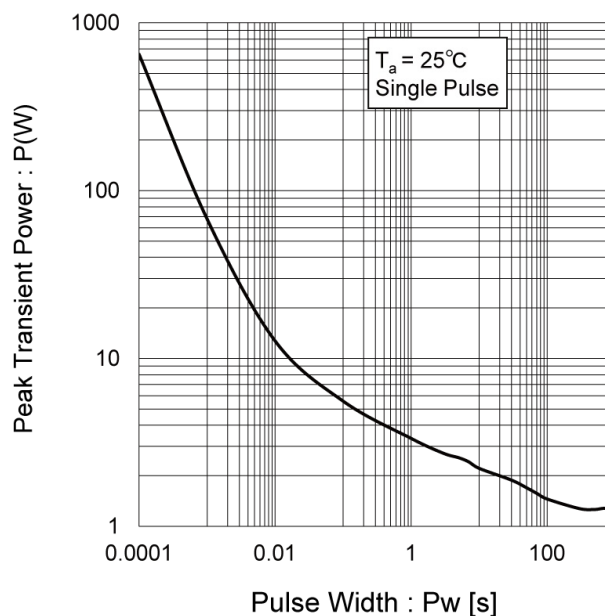


Fig.4 Single Pulse Maximum Power dissipation



●Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)

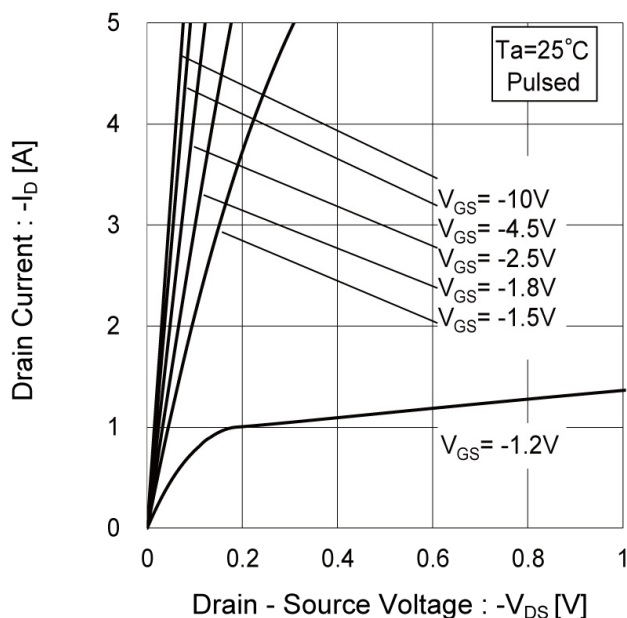


Fig.6 Typical Output Characteristics(II)

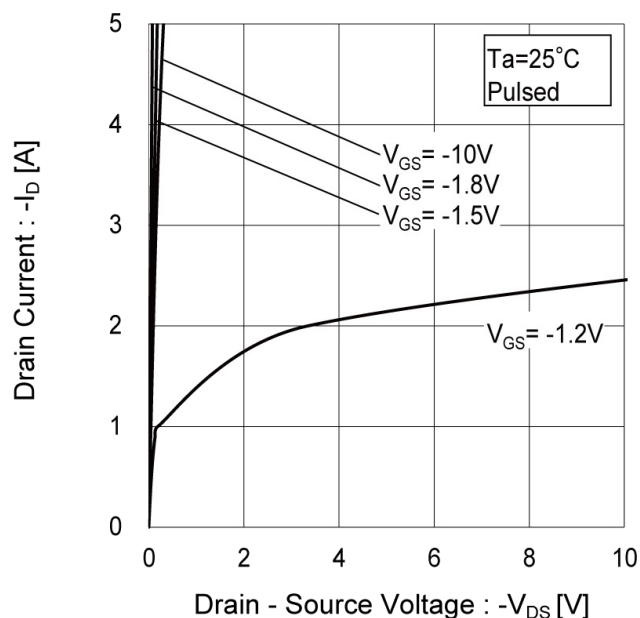


Fig.7 Breakdown Voltage vs. Junction Temperature

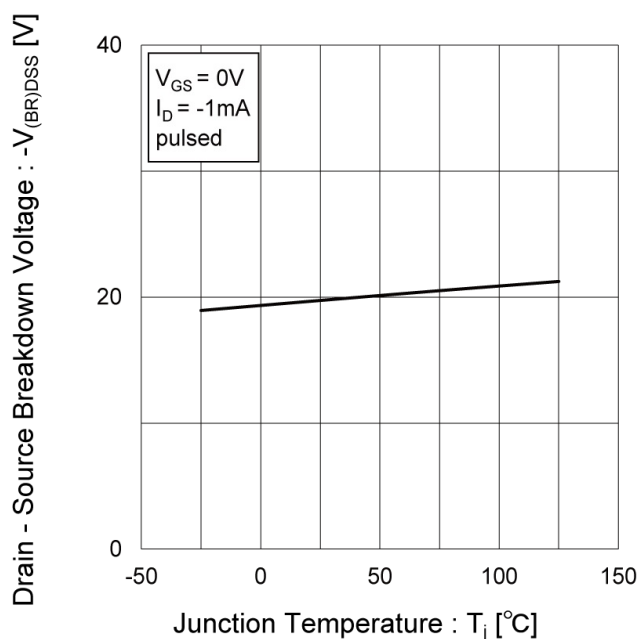
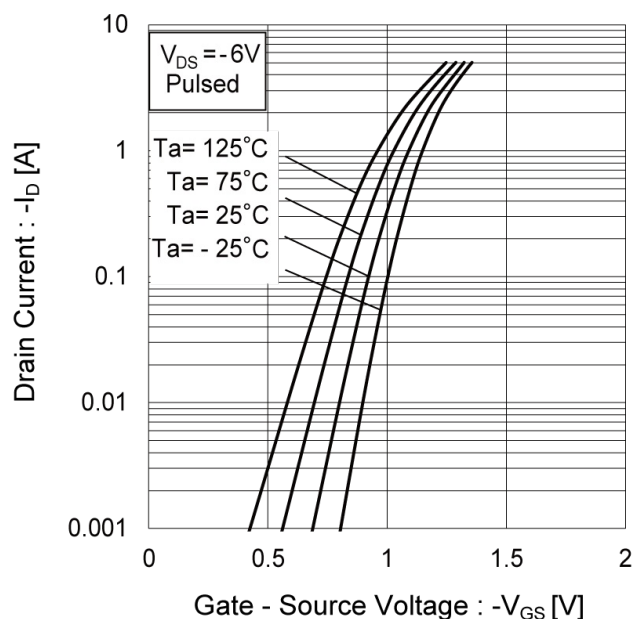


Fig.8 Typical Transfer Characteristics



●Electrical characteristic curves

Fig.9 Gate Threshold Voltage vs.
Junction Temperature

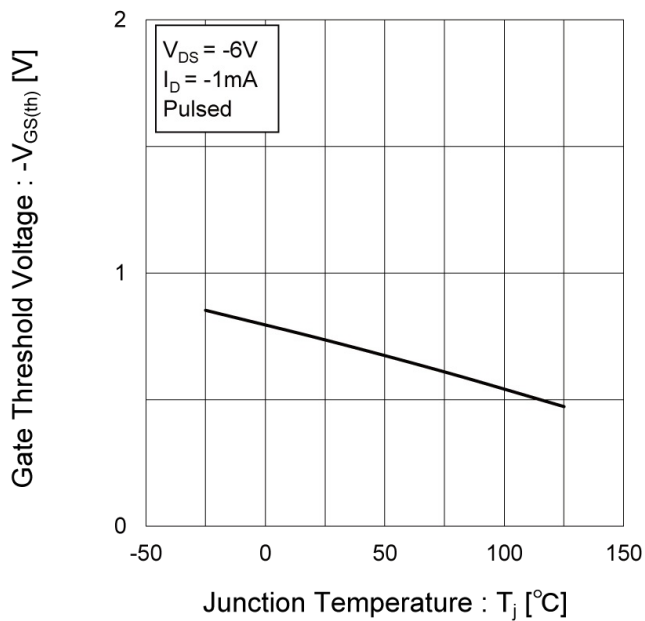


Fig.10 Forward Transfer Admittance vs.
Drain Current

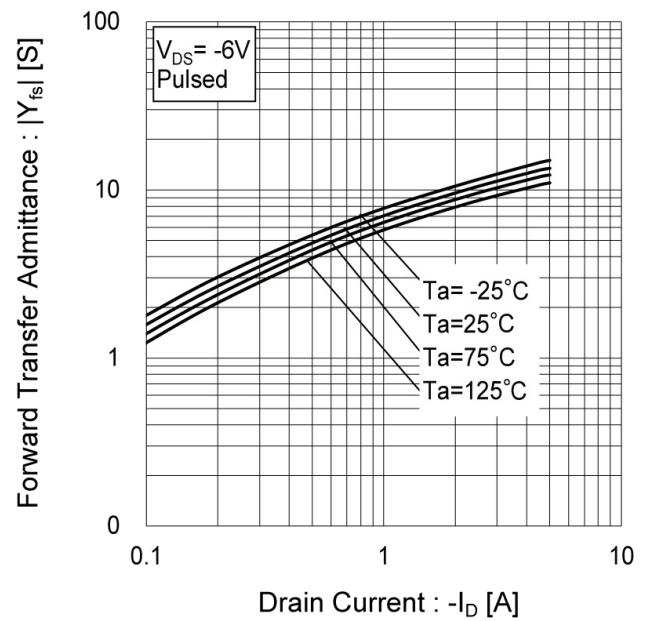


Fig.11 Drain Current Derating Curve

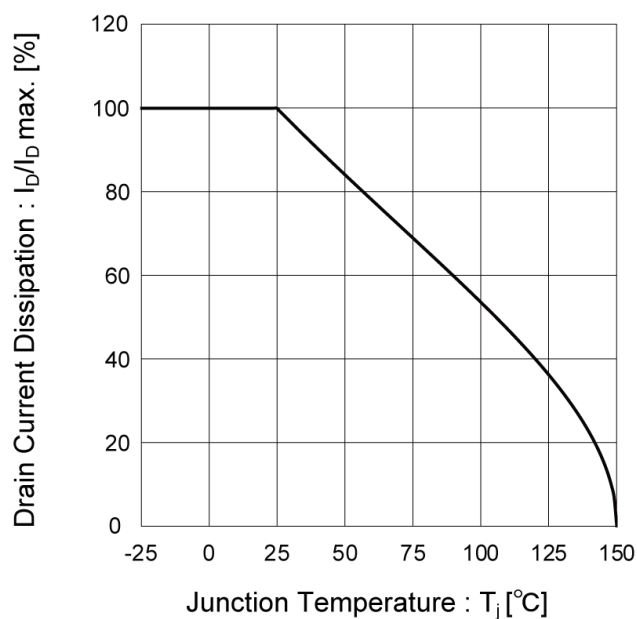
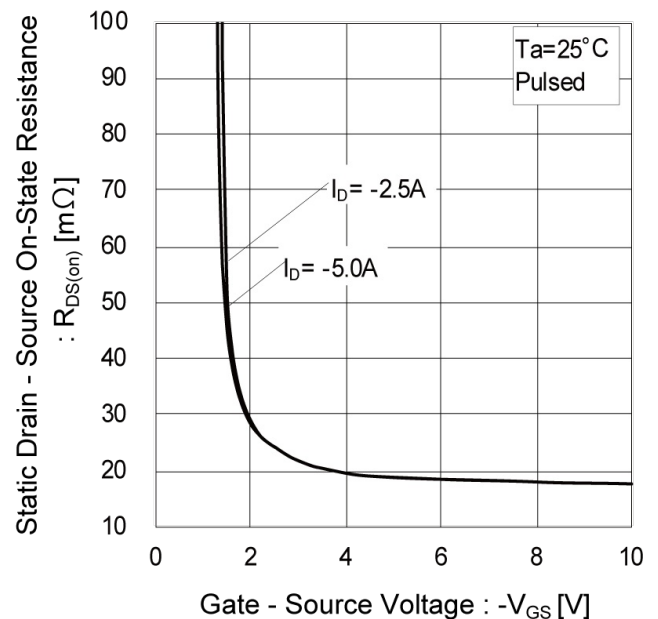


Fig.12 Static Drain - Source On - State
Resistance vs. Gate Source Voltage



●Electrical characteristic curves

Fig.13 Static Drain - Source On - State
Resistance vs. Junction Temperature

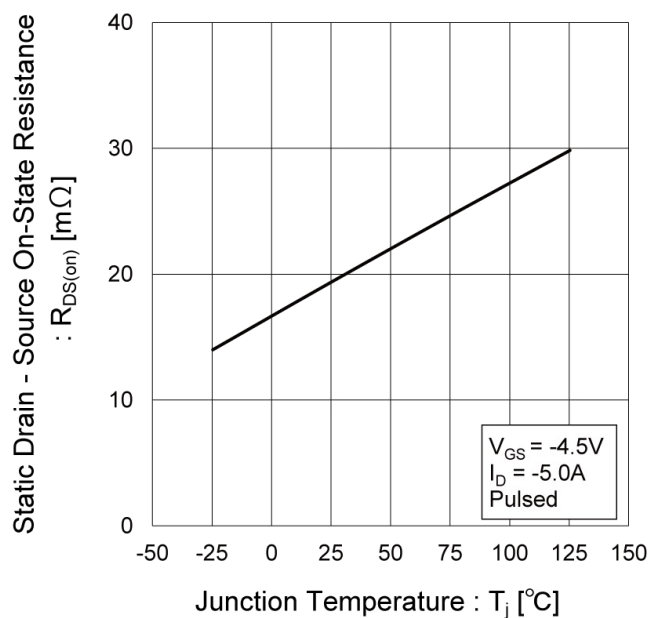
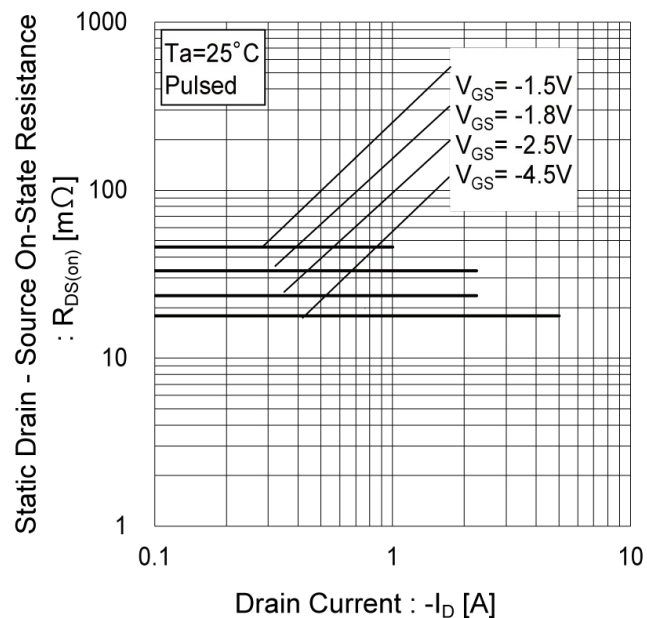


Fig.14 Static Drain - Source On - State
Resistance vs. Drain Current(I)



●Electrical characteristic curves

Fig.15 Static Drain - Source On - State Resistance vs. Drain Current (II)

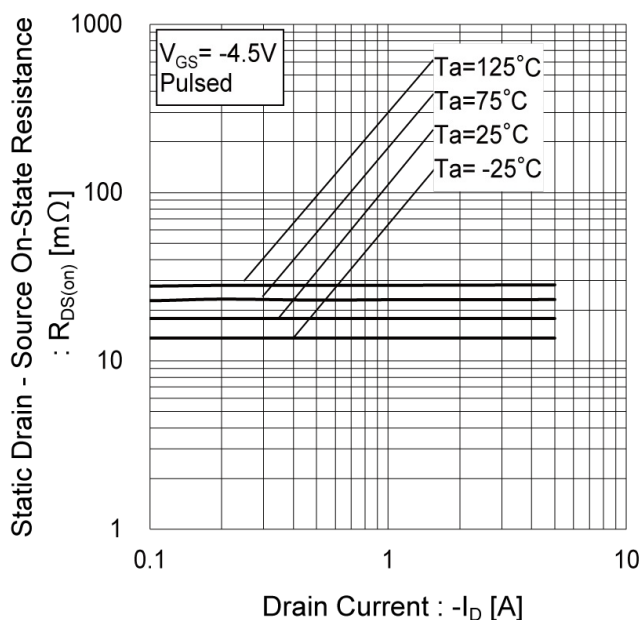


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current (III)

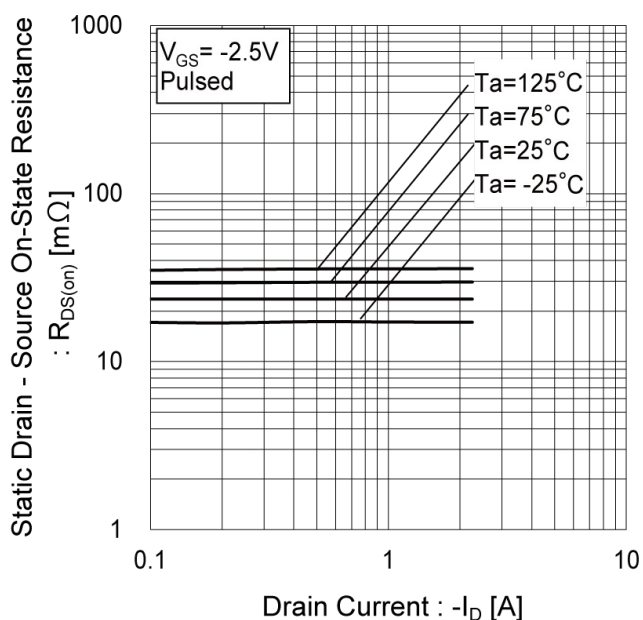


Fig.17 Static Drain - Source On - State Resistance vs. Drain Current (IV)

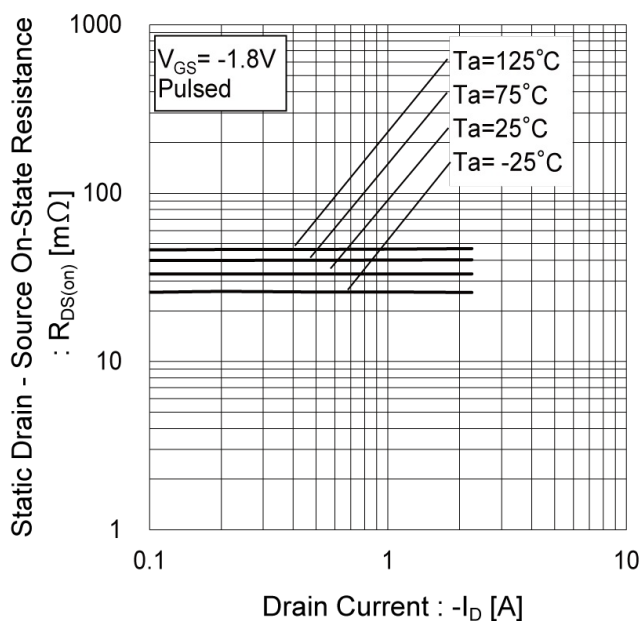
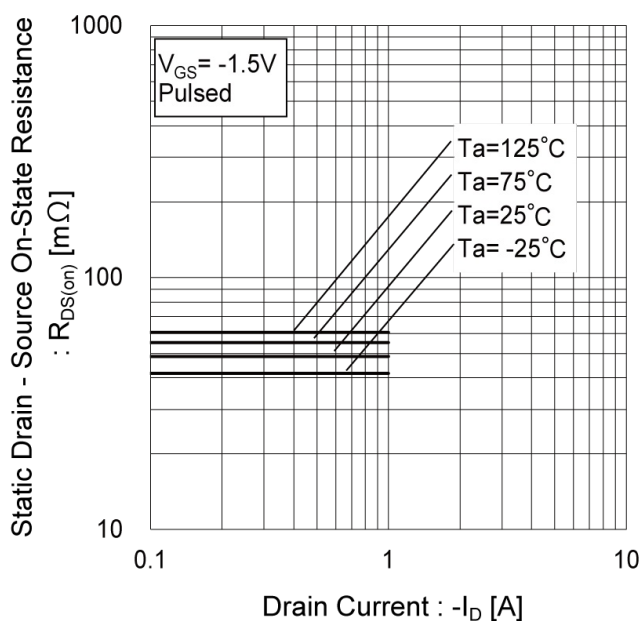


Fig.18 Static Drain - Source On - State Resistance vs. Drain Current (V)



●Electrical characteristic curves

Fig.19 Typical Capacitance vs.
Drain - Source Voltage

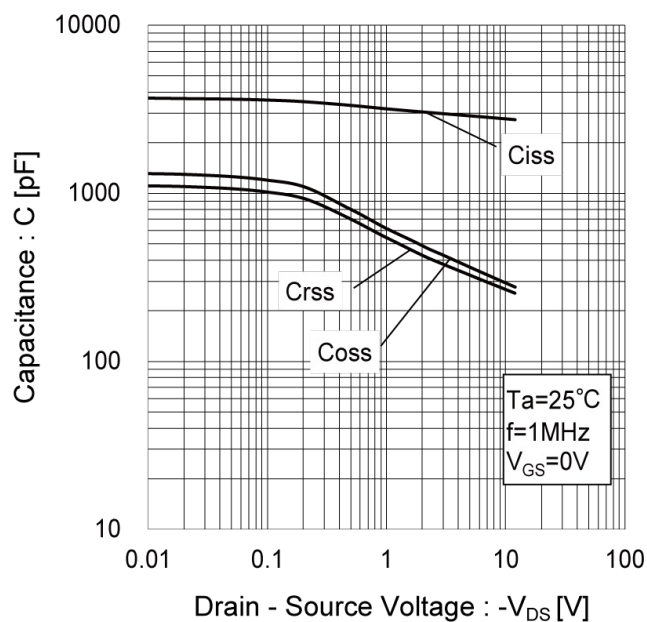


Fig.20 Switching Characteristics

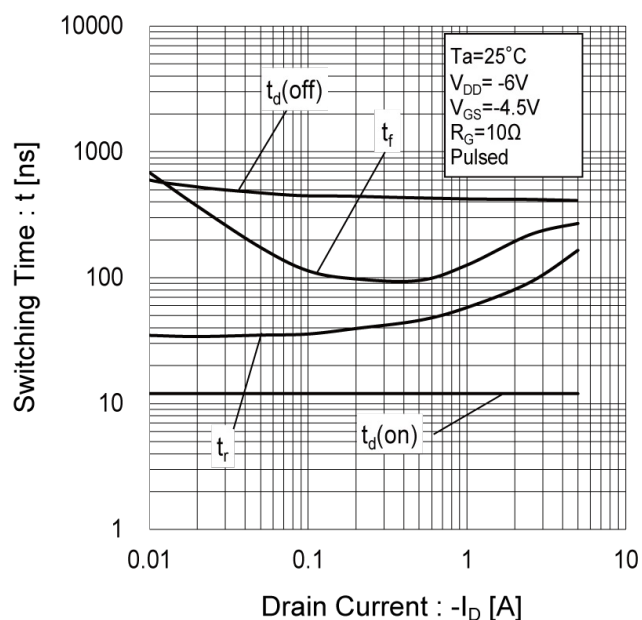


Fig.21 Dynamic Input Characteristics

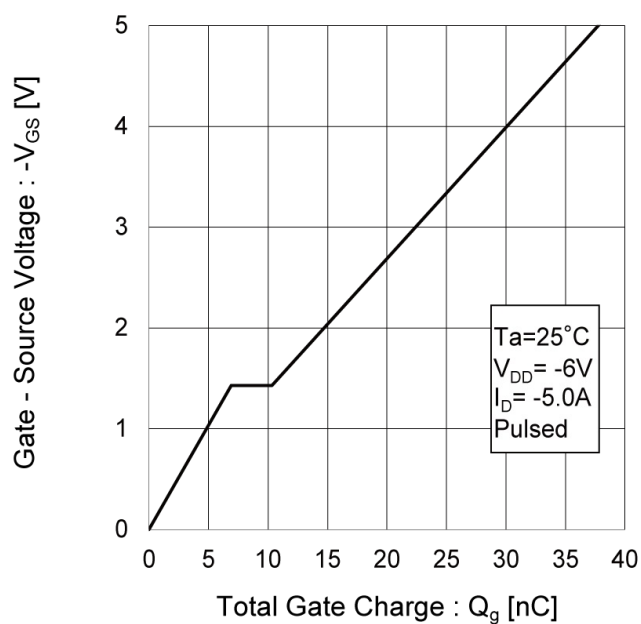
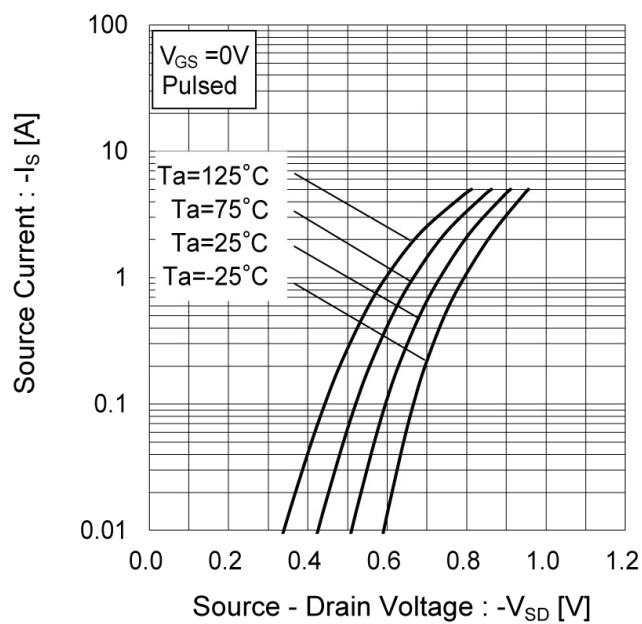


Fig.22 Source Current vs.
Source Drain Voltage



● Measurement circuits

Fig. 1-1 SWITCHING TIME MEASUREMENT CIRCUIT

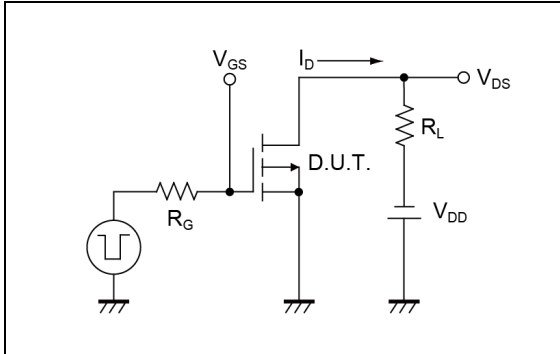


Fig. 1-2 SWITCHING WAVEFORMS

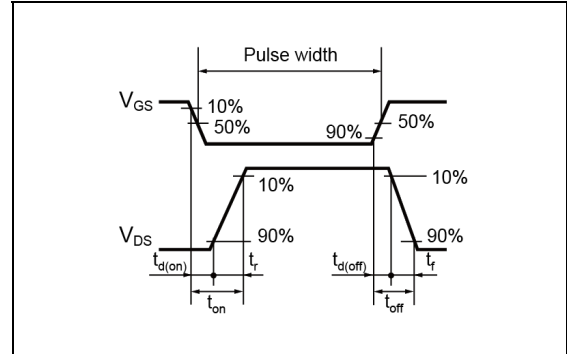


Fig. 2-1 GATE CHARGE MEASUREMENT CIRCUIT

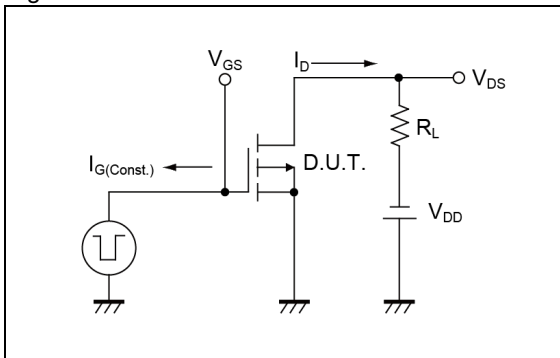
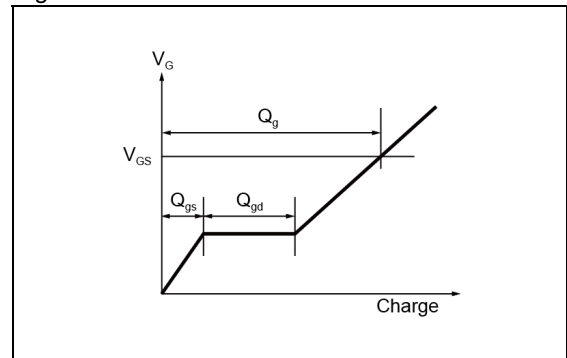


Fig. 2-2 GATE CHARGE WAVEFORM

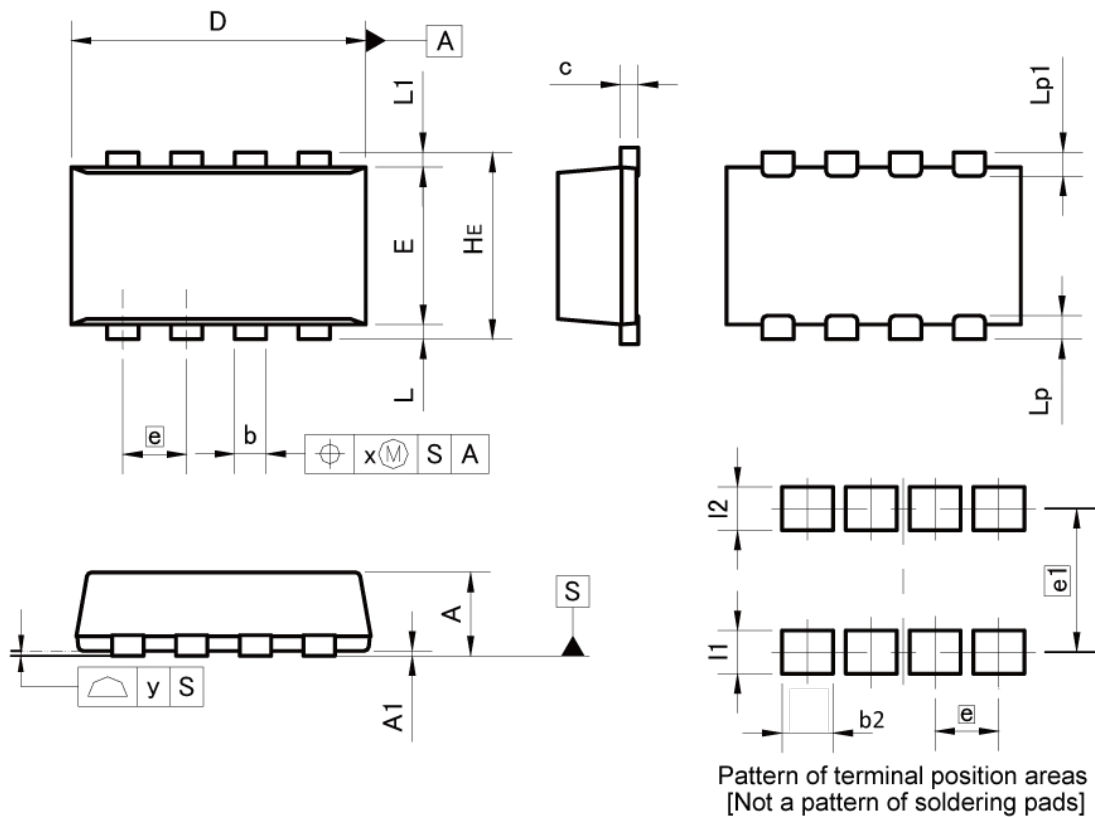


● Notice

This product might cause chip aging and breakdown under the large electrified environment.
Please consider to design ESD protection circuit.

●Dimensions

TSST8



DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.75	0.85	0.030	0.033
A1	0.00	0.05	0.000	0.002
b	0.22	0.42	0.009	0.017
c	0.12	0.22	0.005	0.009
D	2.90	3.10	0.114	0.122
E	1.50	1.70	0.059	0.067
e	0.65		0.026	
HE	1.80	2.00	0.071	0.079
L	0.05	0.25	0.002	0.010
L1	0.05	0.25	0.002	0.010
Lp	0.15	0.34	0.006	0.013
Lp1	0.15	0.34	0.006	0.013
x	-	0.10	-	0.004
y	-	0.10	-	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	-	0.52	-	0.020
e1	1.46		0.057	
l1	-	0.44	-	0.017
l2	-	0.44	-	0.017

Dimension in mm/inches

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